

## **ABSTRACT**

### **SEMICONDUCTOR MEMORY DEVICE AND MANUFACTURING METHOD OF SEMICONDUCTOR MEMORY DEVICE**

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A semiconductor memory device and manufacturing method of the semiconductor memory device are disclosed. A semiconductor memory device includes: a stack structure including a first interlayer insulating layer, and a plurality of second interlayer insulating layers and a plurality of conductive patterns, which are alternately disposed under the first interlayer insulating layer; a hole penetrating the stack structure; a core insulating pattern, a memory pattern, and a channel pattern, disposed inside the hole; and a doped semiconductor layer disposed over the first interlayer insulating layer, the doped semiconductor layer extending to the inside of the hole.

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FIG. 3A

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